

isc Silicon NPN Power Transistor

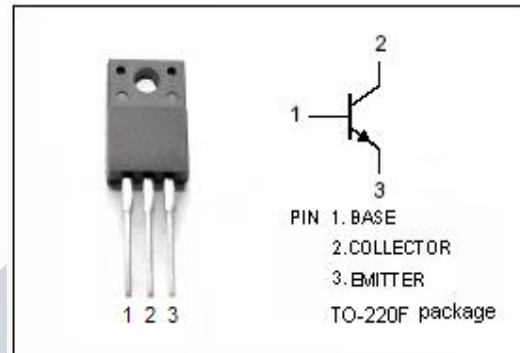
2SC4552

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CE(SUS)} = 60V(\text{Min})$
- High DC Current Gain-
: $h_{FE} = 100(\text{Min})@ (V_{CE} = 2V, I_C = 3A)$
- Low Saturation Voltage-
: $V_{CE(sat)} = 0.3V(\text{Max})@ (I_C = 8A, I_B = 0.4A)$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

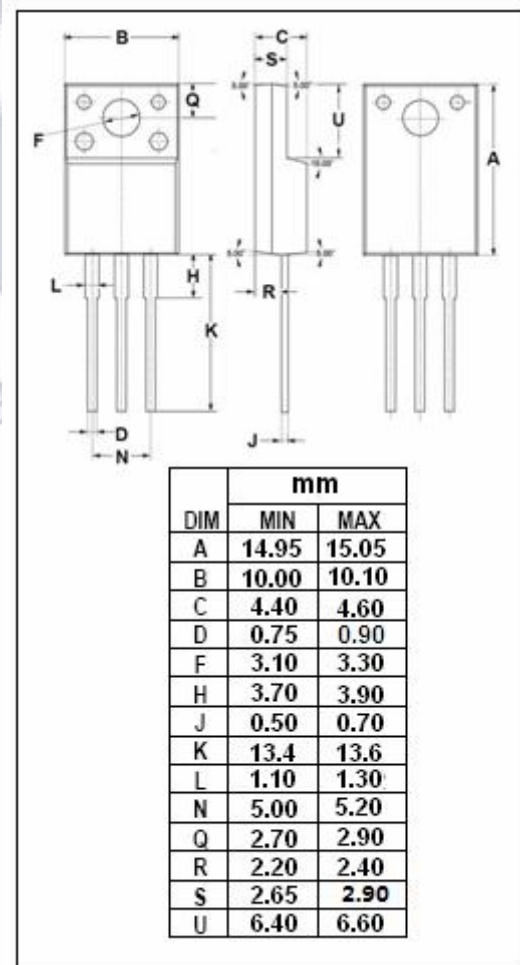
APPLICATIONS

- Designed for use as a driver in DC/DC converters and actuators.



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	7.0	V
I_C	Collector Current-Continuous	15	A
I_{CM}	Collector Current-Pulse	30	A
I_B	Base Current-Continuous	7.5	A
P_T	Total Power Dissipation @ $T_C=25^\circ\text{C}$	30	W
	Total Power Dissipation @ $T_a=25^\circ\text{C}$	2.0	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



isc Silicon NPN Power Transistor**2SC4552****ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C =50mA, I _B =0	60			V
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = 8A; I _B = 0.4A			0.3	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _C = 12A; I _B = 0.6A			0.5	V
V _{BE(sat)-1}	Base-Emitter Saturation Voltage	I _C = 8A; I _B = 0.4A			1.2	V
V _{BE(sat)-2}	Base-Emitter Saturation Voltage	I _C = 12A; I _B = 0.6A			1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 60V; I _E = 0			10	μA
I _{CEO}	Collector Cutoff Current	V _{CE} = 60V; I _B =0			1.0	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			10	μA
h _{FE-1}	DC Current Gain	I _C = 1.5A; V _{CE} = 2V	100			
h _{FE-2}	DC Current Gain	I _C = 3A; V _{CE} = 2V	100		400	
h _{FE-3}	DC Current Gain	I _C = 8A; V _{CE} = 2V	60			
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = 10V; f= 1.0MHz		180		pF
f _T	Current-Gain—Bandwidth Product	I _C = 1.5A; V _{CE} = 10V		120		MHz

Switching times

t _{on}	Turn-on Time	I _C = 8.0A, R _L = 6.3Ω, I _{B1} = -I _{B2} = 0.4A, V _{CC} ≈ 50V			0.3	μs
t _{stg}	Storage Time				1.5	μs
t _f	Fall Time				0.3	μs

◆ h_{FE-2} Classifications

M	L	K
100-200	150-300	200-400